			W			
		\ U I				IEET
100				WWLI		

Name: Alexicol	Date:	_ Date:			
TA:	Section:				

Answer the following questions using information obtained from lecture, the textbook, or lab manual. The responses will be collected at the **beginning of recitation** and checked at the start of your lab section for credit.

1. Define p-type semiconductor and n-type semiconductor.

**2.** Explain how doping silicon with either phosphorous or gallium increases the electrical conductivity over that of pure silicon.

**3.** The Group 3A/Group 5A semiconductors are composed of equal amounts of atoms from Group 3A and Group 5A—for example, InP and GaAs. These types of semiconductors are used in light-emitting diodes and solid-state lasers. What would you add to make a p-type semiconductor from pure GaAs? How would you dope pure GaAs to make an n-type semiconductor?

**4.** The band gap in aluminum phosphide (AlP) is 2.5 electronvolts. What wavelength of light is emitted by an AlP diode? Show work.

$$E_{ph} = \frac{hc}{\lambda} \qquad lev = 1.602 \cdot 10^{-19} \quad \begin{cases} \lambda = \frac{6.626 \cdot 10^{-34} \cdot 3.0 \cdot 10^{-6}}{4.005 \cdot 10^{-19}} = 4.963 \, \text{fm} \end{cases}$$

$$\lambda = \frac{hc}{E_{ph}} \qquad \qquad = \frac{4.963 \, \text{fm}}{4.005 \cdot 10^{-19}} = \frac{4.963$$

**5.** An aluminum antimonide solid-state laser emits light with a wavelength of 730 nm. Calculate the band gap in joules. Show work.

$$Fph = \frac{6.626.10^{34} \cdot 3.0.10^{8}}{(230/1.10^{9})} = 2.72 \cdot 10^{-19} \text{ J}$$

**6.** Explain the difference between the *intrinsic band gap* and the *active* or *optical band gap*.

intrinsic: Mandgap and undoped band gap (not changed by any doping)

active: bandgap that heads to visible photon emissions (band gap other

doping)